# MBRS1035 THRU MBRS1060

# SCHOTTKY BARRIER RECTIFIER

### REVERSE VOLTAGE: FORWARD CURRENT:

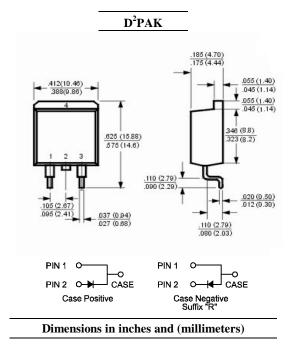
### 35 to 60 VOLTS 10.0 AMPERE

#### FEATURES

- $\cdot$  For surface mounted application
- $\cdot$  Metal silicon junction, majority carrier conduction
- $\cdot$  Guard ring for overvoltage protection
- $\cdot$  Low power loss, high efficiency
- For use in low voltage, high frequency inverters, free whelling, and polarity protection applications
- High temperature soldering guaranteed: 250°C/10 seconds, 0.25" (6.35mm) from case

#### MECHANICAL DATA

Case: Molded plastic, D<sup>2</sup>PAK Epoxy: UL 94V-O rate flame retardant Terminals: Leads solderable per MIL-STD-202 method 208 guaranteed Polarity: As marked Mounting position: Any Weight: 0.06ounce, 1.70gram



#### Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave,  $60H_Z$ , resistive or inductive load. For capacitive load, derate current by 20%.

	Symbols	<b>MBRS1035</b>	<b>MBRS1045</b>	MBRS1050	MBRS1060	Units
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	35	45	50	60	Volts
Maximum RMS Voltage	V <sub>RMS</sub>	24	31	35	42	Volts
Maximum DC Blocking Voltage	V <sub>DC</sub>	20	30	40	50	Volts
Maximum Average Forward Rectified Current See Fig. 1	I <sub>(AV)</sub>	10.0				Amp
Peak repetitive forward current (sq. wave, 20 KHz) at $T_{\rm C}$ = 135°C	I <sub>FRM</sub>	20				Amp
Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load (JEDEC method)	I <sub>FSM</sub>	150				Amp
Peak repetitive reverse current at tp = 2.0µs, 1KHz	I <sub>RRM</sub>	1.0		0.5		Amp
$\begin{array}{c} \text{at } \mathbf{I}_{\mathrm{F}} = 10 \mathrm{A}, \ \mathbf{T}_{\mathrm{C}} = 25^{\circ} \mathrm{C} \\ \text{Maximum Forward} \\ \text{Voltage (Note 1)} \\ \text{at } \mathbf{I}_{\mathrm{F}} = 10 \mathrm{A}, \ \mathbf{T}_{\mathrm{C}} = 125^{\circ} \mathrm{C} \\ \text{at } \mathbf{I}_{\mathrm{F}} = 20 \mathrm{A}, \ \mathbf{T}_{\mathrm{C}} = 25^{\circ} \mathrm{C} \\ \text{at } \mathbf{I}_{\mathrm{F}} = 20 \mathrm{A}, \ \mathbf{T}_{\mathrm{C}} = 125^{\circ} \mathrm{C} \end{array}$	V <sub>F</sub>	- 0.57 0.84 0.72		0.80 0.70 0.95 0.85		Volts
Maximum Reverse Currentat $T_C=25^{\circ}C$ at Rated DC Blocking Voltage $T_C=125^{\circ}C$	I <sub>R</sub>	0.1 15				mAmp
Voltage rate of change (rated V <sub>R</sub> )	dv/dt	10,000				V/µs
Typical Thermal Resistance	R <sub>0JC</sub>	2.0				°C/W
Operating Temperature Range	T <sub>J</sub>	-55 to +150				ĉ
Storage Temperature Range	Tstg	-55 to +175				°C

#### NOTES:

1- Pulse test: 300µs pulse width, 1% duty cycle



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#### RATINGS AND CHARACTERISTIC CURVES

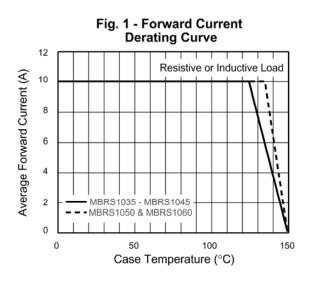


Fig. 3 - Typical Instantaneous Forward Characteristics

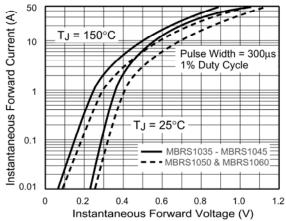


Fig. 5 - Typical Junction Capacitance 4,000 TJ = 25°C f = 1.0 MHz Junction Capacitance (pF) Vsig = 50mVp-p 1,000 MBRS1035 - MBRS1045

-MBRS1050 & MBRS1060 

1

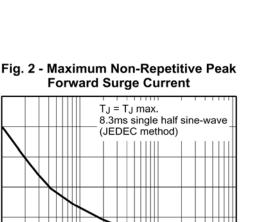
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Reverse Voltage (V)

100

100

0.1



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Peak Forward Surge Current (A) 100 75 50 25 0.1 1 10 100 Number of Cycles at 60 Hz

175

150

125

Fig. 4 - Typical Reverse Characteristics

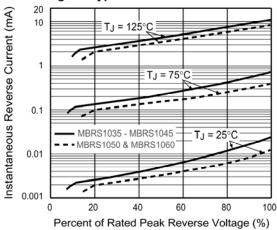


Fig. 6 - Typical Transient Thermal Impedance

